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SYMBOL AND ABBREVIATION LISTS

EH₀: quasi-TEM mode

EH₁: first higher-order mode

Quasi-TEM: quasi-transverse electromagnetic

CCS: Complementary-Conducting-Strip

CCSs: Complementary Conducting Strips

MS: microstrip

MSs: microstrips

TL: transmission line

TLs: transmission lines

CMOS: Complementary Metal-Oxide-Semiconductor

TSMC: Taiwan Semiconductor Manufacturing Company

1P5M: one ploy and five metal layers

MIM: Metal-Isolator-Metal

2-D TL: two-dimensional transmission line

Z_c: characteristic impedance

SWF: slow-wave factor

MICs: microwave integrated circuits

MIC: microwave integrated circuit

 S_p : power-wave scattering parameter matrix

 γ : propagation constant, $\gamma = j\beta + \alpha$ ($e^{j\omega t} e^{-\gamma}$ assumed)

 β : phase constant

 α : attenuation constant

Re(Z_c): real part of characteristic impedance

Im(Z_c): imaginary part of characteristic impedance

k_o: the free-space wave number $\left(=\frac{2\pi}{\lambda_o} \text{ or } \frac{2\pi f}{c}\right)$

 β/k_o : normalized phase constant

 α/k_o : normalized attenuation constant

 λ_g : the guided wavelength

 λ_o : the free-space guided wavelength

D.C., DC: direct current

LTCCs: low-temperature co-fired ceramics

PCBs: printed circuit boards

MMIC: monolithic microwave integrated circuit

MMICs: monolithic microwave integrated circuits

GaAs: gallium arsenide

ε_r: relative permittivity

 μ_r : relative permeability

MIS: metal-insulator-semiconductor

MS: microstrip

SWF: slow-wave factor

TFMSs: thin-film microstrips

TFMS: thin-film microstrip

HMICs: hybrid microwave integrated circuits

HMIC: hybrid microwave integrated circuit

SiON: silicon oxynitride

CPW: coplanar waveguide

PLL: phase-locked-loop

DIL: dielectric imaging line

1-D: one-dimensional

2-D: two-dimensional

pHEMT: pseudomorphic high electron-mobility transistor

ARF: area reduction factor

Z_o: referenced impedance, typically equal to 50 ohm



SMA: subminiature A
BFN: Beam forming network
UC-PBG: uniplanar compact photonic-bandgap
EME: electric-magnetic-electric
2-D TL: two-dimensional transmission-line
RFIC: radio frequency integrated circuit
RFICs: radio frequency integrated circuits
RF: radio frequency

